

IN THE CLAIMS

Please cancel claims 1, 10, and in place thereof substitute new claims 11-20 as follows:

*Suh C*

11. A method for removing a deposited film inside a chamber which comprises:  
providing a hot element in the chamber, the hot element having at least a surface  
which comprises platinum;  
exhausting said chamber;  
5 heating the hot element;  
supplying a cleaning gas into the chamber;  
contacting the cleaning gas with the heated hot element to decompose and/or  
activate the cleaning gas and generate an activated species therefrom;  
allowing the activated species to convert the deposited film into a gaseous  
10 substance; and  
removing the gaseous substance from the chamber. - -

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12. The method according to claim 11, wherein said chamber comprises a CVD  
apparatus and the method further comprises:

15 heating the hot element;  
supplying a material gas to the chamber;  
contacting the material gas with the hot element to cause decomposition and/or  
activation of the material gas by said hot element; and  
forming the deposited film which comprises at least one element from said  
material gas on a substrate. - -

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13. The method according to claim 11, wherein at least a part of a surface of an  
inner structure of said chamber is covered with platinum. - -

14. The method according to claim 12, wherein at least a part of the surface of  
an inner structure of said chamber is covered with platinum. - -

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~~--15. The method according to claim 11, wherein said cleaning gas is a gas containing at least one of fluorine (F<sub>2</sub>), chlorine (Cl<sub>2</sub>), nitrogen trifluoride (NF<sub>3</sub>), carbon tetrafluoride (CF<sub>4</sub>), hexafluoroethane (C<sub>2</sub>F<sub>6</sub>), octafluoropropane (C<sub>3</sub>F<sub>8</sub>), carbon tetrachloride (CCl<sub>4</sub>), pentafluorochloroethane (C<sub>2</sub>ClF<sub>5</sub>), trifluorochlorine (ClF<sub>3</sub>), trifluorochloromethane (CClF<sub>3</sub>), and sulfur hexafluoride (SF<sub>6</sub>), and mixtures thereof.~~

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~~--16. The method according to claim 12, wherein said cleaning gas is a gas containing at least one of fluorine (F<sub>2</sub>), chlorine (Cl<sub>2</sub>), nitrogen trifluoride (NF<sub>3</sub>), carbon tetrafluoride (CF<sub>4</sub>), hexafluoroethane (C<sub>2</sub>F<sub>6</sub>), octafluoropropane (C<sub>3</sub>F<sub>8</sub>), carbon tetrachloride (CCl<sub>4</sub>), pentafluorochloroethane (C<sub>2</sub>ClF<sub>5</sub>), trifluorochlorine (ClF<sub>3</sub>), trifluorochloromethane (CClF<sub>3</sub>), sulfur hexafluoride (SF<sub>6</sub>), and mixtures thereof.~~

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~~--17. A CVD apparatus comprising:  
a chamber having a material gas inlet and a cleaning gas inlet;  
a hot element located in the chamber, the hot element having a surface which comprises platinum;  
means for exhausting the chamber;  
a source of material gas coupled to the material gas inlet;  
means for heating the hot element to a first temperature sufficient to decompose and/or activate the material gas;  
a source of cleaning gas coupled to the cleaning gas inlet; and  
means for heating the hot element to a second temperature sufficient to decompose and/or activate the cleaning gas to generate an activated species therefrom which active species is able to convert a film deposited inside said chamber to gaseous substance, which gaseous substance can be removed from the chamber by exhausting the chamber.~~

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~~--18. The CVD apparatus according to claim 17, wherein at least a part of a surface of an inner structure of said chamber is covered with platinum.~~